EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(((silicon near substrate) (semiconductor near substrate) wafer) with (depression recess apperture aperture) with (contuctive near1 (hole via)) with (insulat$3 dielectric) with ((flush$3 coplanar) with surface)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:03
L2	0	(((silicon near substrate) (semiconductor near substrate) wafer) same (depression recess apperture aperture) same (contuctive near1 (hole via)) same (insulat$3 dielectric) same ((flush$3 coplanar) with surface)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:04
L3	0	(((silicon near substrate) (semiconductor near substrate) wafer) and (depression recess apperture aperture) and (contuctive near1 (hole via)) and (insulat$3 dielectric) and ((flush$3 coplanar) with surface)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:04

L5	4	(((silicon near substrate) (semiconductor near substrate) wafer) with ((((interconnect$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) with (insulat$3 dielectric)). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:09
L6	5	(((silicon near substrate) (semiconductor near substrate) wafer) same ((((interconnect$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) same (insulat$3 dielectric)). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:10
L7	14	(((silicon near substrate) (semiconductor near substrate) wafer) and ((((interconnect$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) and (insulat$3 dielectric)). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:10
L8	10	7 not 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:10

L9	243	"257"/$.ccls. and ((silicon near substrate) (semiconductor near substrate) wafer) and (((interconnect$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) and (insulat$3 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:12
L10	137	"438"/$.ccls. and ((silicon near substrate) (semiconductor near substrate) wafer) and (((interconnect$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) and (insulat$3 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:13
L11	249	9 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:13
L12	173	11 and (conductive near1 (hole vias))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:13

4/13/2009 10:15:00 AM
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